Electronic Information Disclosure Statement

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High-Power Pulsed Magnetron Sputtering

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Application:	10/065277
Confirmation:	5690
Applicant(s):	Roman Chistyakov
Docket Number:	ZON-001
Group Art Unit:	1753
Examiner:	Unassigned
search string:	(5015493 or 6296742 or 6413382 or 6436251 or 5875207 or 4953174 or 6296742 or 4965248).pn.

US Patent Documents

Note: Applicant is not required to submit a paper copy of cited US Patent Documents

init	Citation No.	Patent Number	Date	Bar Code	Patentee	Class	Subclass
	P01	5015493	1991-05-14		Gruen	427	38
	P02	6296742	2001-10-02		Kouznetsov	204	192.12
	P03	6413382	2002-07-02		Wang et al.	204	192.12
	P04	6436251	2002-08-20		Gopalraja et al.	204	298.12
	P05	5875207	1999-02-23		Osmanow	372	86
	P06	4953174	1990-08-28		Eldridge et al.	372	87
	P07	6296742	2001-10-02		Kouznetsov	204	192.12
	P08	4965248	1990-10-23		Poppe et al.	505	1

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Signature

Examiner Name	Date
Sidney Vincent Bostwick	1-7-04

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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

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Sheet 1 of 3

Complete if Known	
Application Number	10/065,277
Filing Date	9/30/2002
First Named Inventor	Chistyakov
Art Unit	1753
Examiner Name	McDonald
Attorney Docket Number	ZON-001

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U.S. PATENT DOCUMENTS

Examiner Initials*	Cite No.[1]	Document Number Number - Kind Code[2] (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		US-			
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FOREIGN PATENT DOCUMENTS

Examiner Initials*	Cite No.[1]	Foreign Patent Document Country Code[3] - Number[4] - Kind Code[5] (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T[6]
	B1	WO 98/40532	09/17/1998	Chemfilt R. & D. ...		
	B2	WO 01/98553 A1	12/27/2001	Chemfilt R. & D. AB		

Examiner Signature		Date Considered	1-7-04

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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

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Sheet 2 of 3

Complete if Known	
Application Number	10/065,277
Filing Date	9/30/2002
First Named Inventor	Chistyakov
Group Art Unit	1753
Examiner Name	McDonald
Attorney Docket Number	ZON-001

OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No.[1]	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T[2]
	C1	BOOTH, ET AL., The Transition From Symmetric To Asymmetric Discharges In Pulsed 13.56 MHz Capacity Coupled Plasmas, J. Appl. Phys., July 15, 1997, Pgs. 552-560, Vol. 82 (2), American Institute of Physics.	
	C2	BUNSHAH, ET AL., Deposition Technologies For Films And Coatings, Materials Science Series, Pgs. 176-183, Noyes Publications, Park Ridge, New Jersey.	
	C3	DAUGHERTY, ET AL., Attachment-Dominated Electron-Beam-Ionized Discharges, Applied Science Letters, May 15, 1976, Vol. 28, No. 10, American Institute of Physics.	
	C4	GOTO, ET AL., Dual Excitation Reactive Ion Etcher for Low Energy Plasma Processing, J. Vac. Sci. Technol. A, Sept/Oct. 1992, Pgs. 3048-3054, Vol.10, No. 5, American Vacuum Society.	
	C5	KOUZNETSOV, ET AL., A Novel Pulsed Magnetron Sputter Technique Utilizing Very High Target Power Densities, Surface & Coatings Technology, Pgs. 290-293, Elsevier Sciences S.A.	
	C6	LINDQUIST, ET AL., High Selectivity Plasma Etching Of Silicon Dioxide With A Dual Frequency 27/2 MHz Capacitive RF Discharge.	
	C7	MACAK, Reactive Sputter Deposition Process of Al2O3 and Characterization Of A Novel High Plasma Density Pulsed Magnetron Discharge, Linkoping Studies In Science And Technology, 1999, Pgs. 1-2, Sweden.	
	C8	MACAK, ET AL., Ionized Sputter Deposition Using An Extremely High Plasma Density Pulsed Magnetron Discharge, J. Vac. Sci. Technol. A., July/August 2000, Pgs. 1533-37, Vol. 18, No. 4, American Vacuum Society.	

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Sheet 3 of 3

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Application Number	10/065,277
Filing Date	9/30/2002
First Named Inventor	Chistyakov
Group Art Unit	1753
Examiner Name	McDonald
Attorney Docket Number	ZON-001

OTHER PRIOR ART -- NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No.[1]	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published	T[2]
	C9	MOZGRIN, ET AL., High-Current Low-Pressure Quasi -Stationary Discharge In A Magnetic Field: Experimental Research, Plasma Physics Reports, 1995, Pgs. 400-409, Vol. 21, No. 5, Mozgrin, Feitsov, Khodachenko.	
	C10	ROSSNAGEL, ET AL., Induced Drift Currents In Circular Planar Magnetrons, J. Vac. Sci. Technol. A., January/February 1987, Pgs. 88-91, Vol. 5, No. 1, American Vacuum Society.	
	C11	SHERIDAN, ET AL., Electron Velocity Distribution Functions In A Sputtering Magnetron Discharge For The EXB Direction, J. Vac. Sci. Technol. A., July/August 1998, Pgs. 2173-2176, Vol. 16, No. 4, American Vacuum Society.	
	C12	STEINBRUCHEL, A Simple Formula For Low-Energy Sputtering Yields, Applied Physics A., 1985, Pgs. 37-42, Vol. 36, Springer-Verlag.	

Examiner Signature		Date Considered	1-7-04

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